

ABSTRACT OF THE DISCLOSURE

A semiconductor device capable of improving the operating speed and inhibiting the threshold voltage from fluctuation is obtained. In this semiconductor device,
5 fluorine is introduced into at least any of regions extending over the junction interfaces between a first conductivity type semiconductor region and second conductivity type source/drain regions, at least the interface between the gate insulator film and the central
10 region of a channel region as well as a gate insulator film, and side wall insulator films.